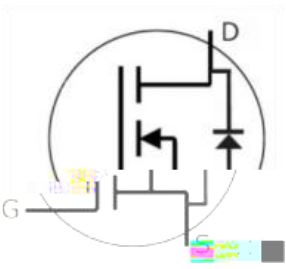


TriQSiC™1200V Silicon Carbide Power MOSFET G3

Features

-
-
-
-
-



Benefits

-
-
-
-
-

Part number	Die size	W x L	mm

Applications

-
-
-
-

Table 1 Key performance and package parameters

Type	V _{DS}	I _{DS}	R _{DS(on)} , typ	T _{J,max}

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1 Maximum ratings

Table 2 **Maximum rating**

Symbol	Parameter	Value	Unit	Test Conditions	Note

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2 Electrical characteristics

2.1 Static characteristics

Table 4 Static characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
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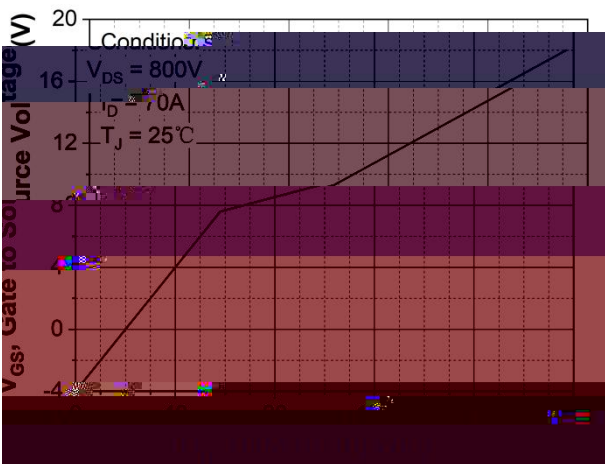
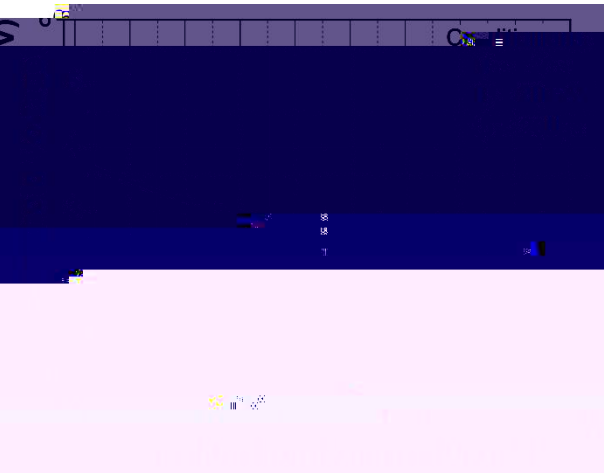
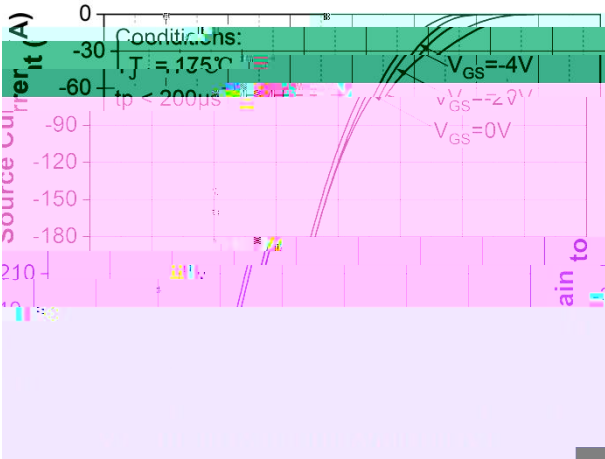
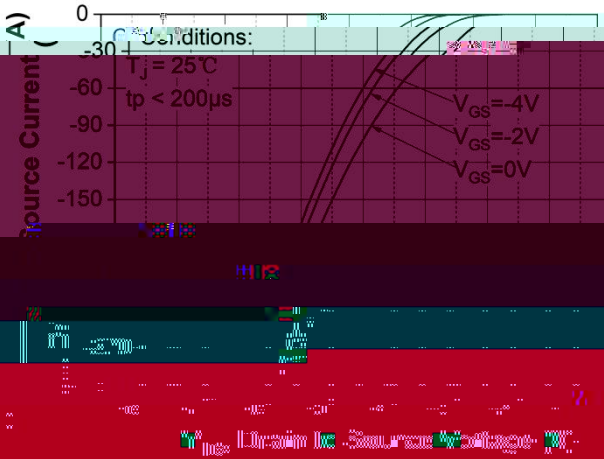
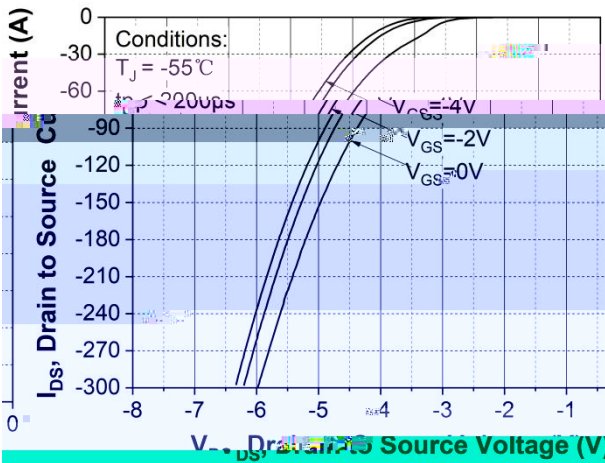
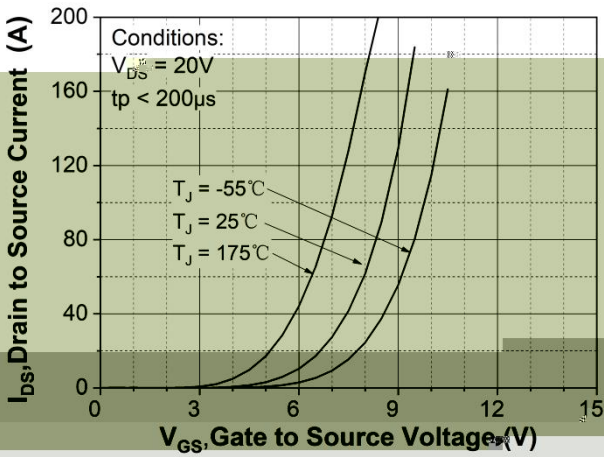
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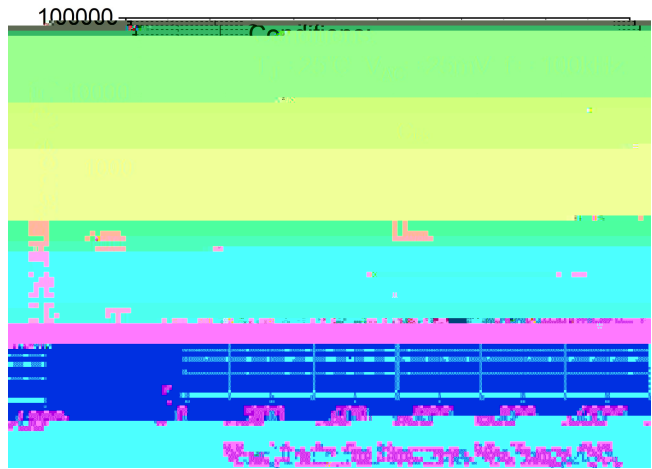
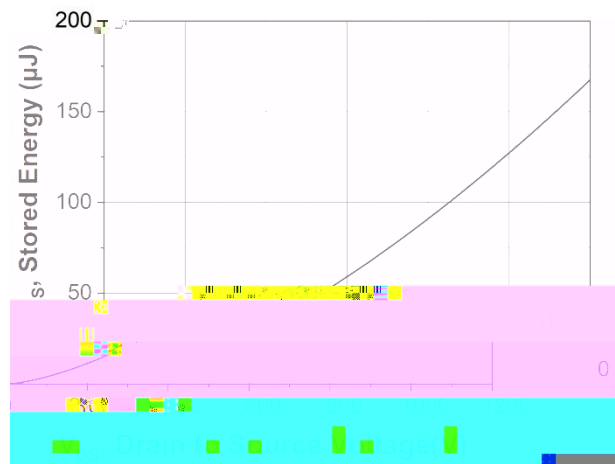
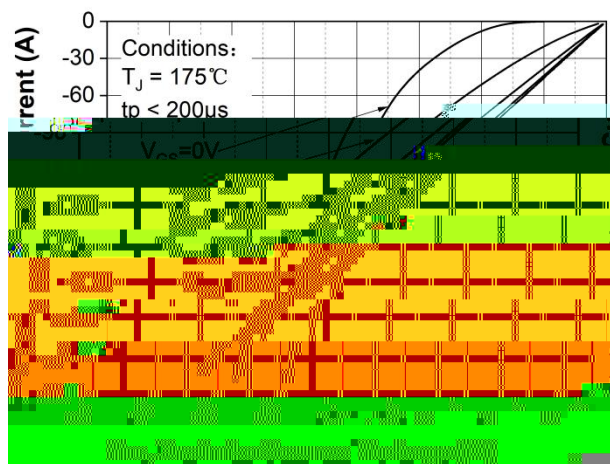
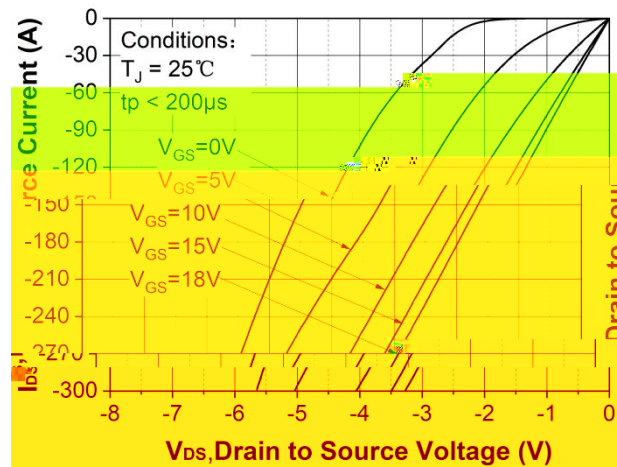
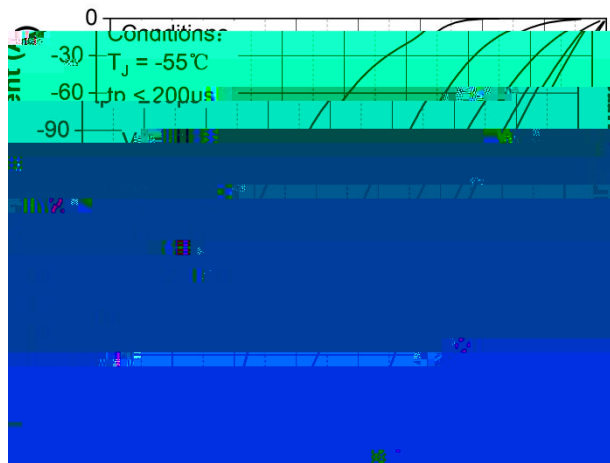
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[illegible]

The diagram shows a rectangular layout with overall dimensions A (height) and B (width). The layout is divided into several regions:

- A blue header bar at the top with height a_2 .
- A yellow footer bar at the bottom with height a_3 .
- A light blue vertical bar on the left with width b_3 .
- A light blue vertical bar on the right with width b_4 .
- A central yellow region with height a_1 and width b_1 , containing a green square labeled G .
- Two gray rectangular regions labeled S , one in the top right and one in the bottom right.

Dimensions are labeled as follows:

- Overall width: B
- Overall height: A
- Header bar height: a_2
- Footer bar height: a_3
- Left bar width: b_3
- Right bar width: b_4
- Central yellow region width: b_1
- Central yellow region height: a_1

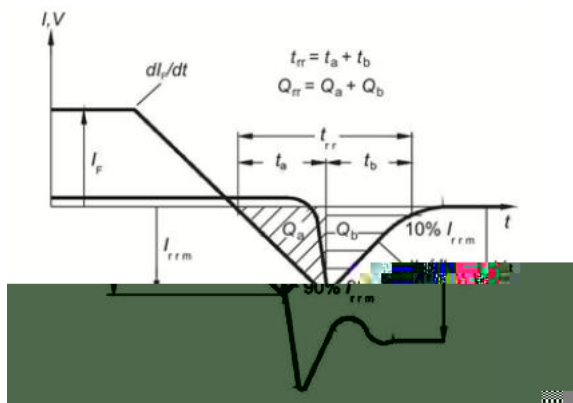
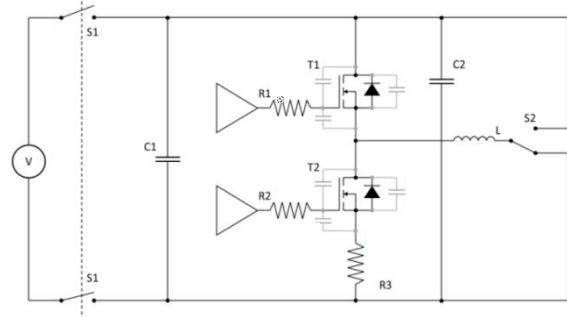
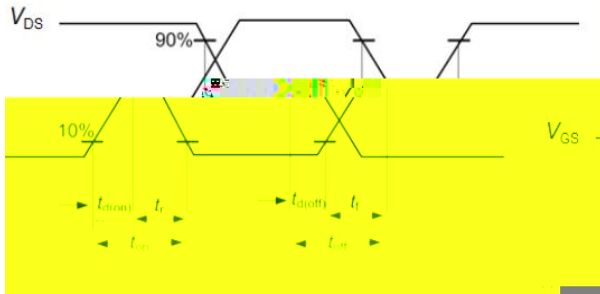
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5 Test conditions



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Revision history

Document version	Date of release	Document stage	Description of changes
V01_00	2026-06-29	Final	

Attention

RoHS compliance

REACH compliance

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